

Features

- Typ. $R_{DS(on)} = 13.5\text{ m}\Omega$ @ $V_{GS} = 18\text{ V}$
 Typ. $R_{DS(on)} = 18\text{ m}\Omega$ @ $V_{GS} = 15\text{ V}$
- Ultra Low Gate Charge ($Q_{G(tot)} = 262\text{ nC}$)
- High Speed Switching with Low Capacitance ($C_{oss} = 365\text{ pF}$)
- 100% Avalanche Tested
- $T_J = 175^\circ\text{C}$
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Typical Applications

- Solar Inverters
- Electric Vehicle Charging Stations
- Uninterruptable Power Supplies (UPS)
- Energy Storage Systems
- Switch Mode Power Supplies (SMPS)

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
		-	
		-	
		-	

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Table 2. ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SOURCE-DRAIN DIODE CHARACTERISTICS						
		-	-		-	
		μ	-		-	
			-		-	μ
			-		-	
			-		-	
			-		-	

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TYPICAL CHARACTERISTICS

TYPICAL CHARACTERISTICS

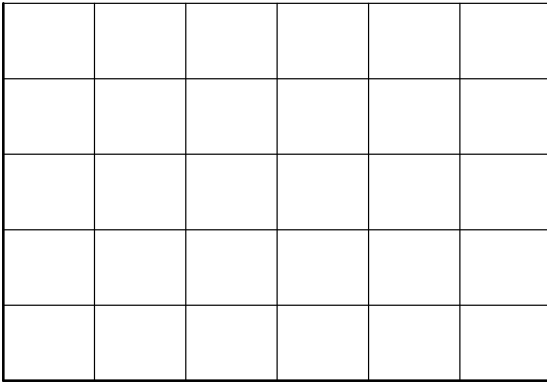


Figure 7. Gate-to-Source Voltage vs. Total Charge

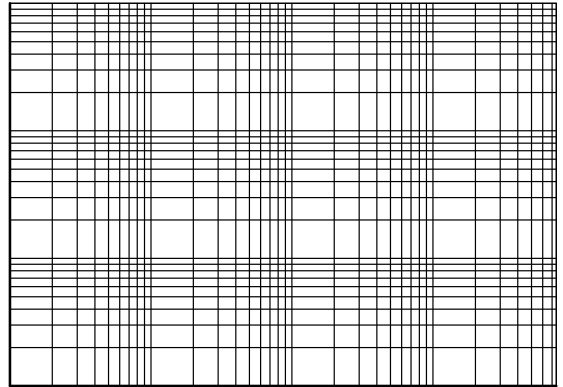


Figure 8. Capacitance vs. Drain-to-Source Voltage

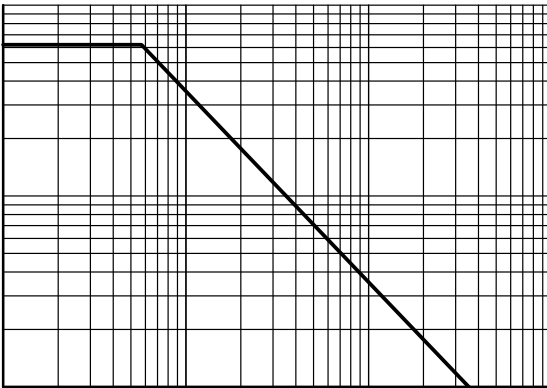


Figure 9. Unclamped Inductive Switching Capability

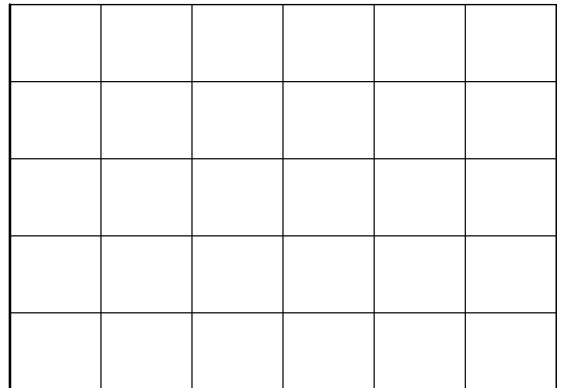
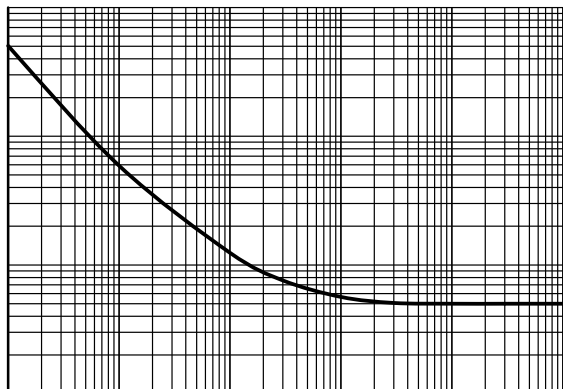
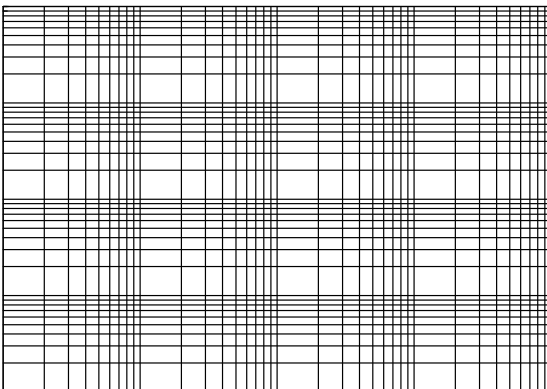


Figure 10. Maximum Continuous Drain Current vs. Case Temperature



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TYPICAL CHARACTERISTICS

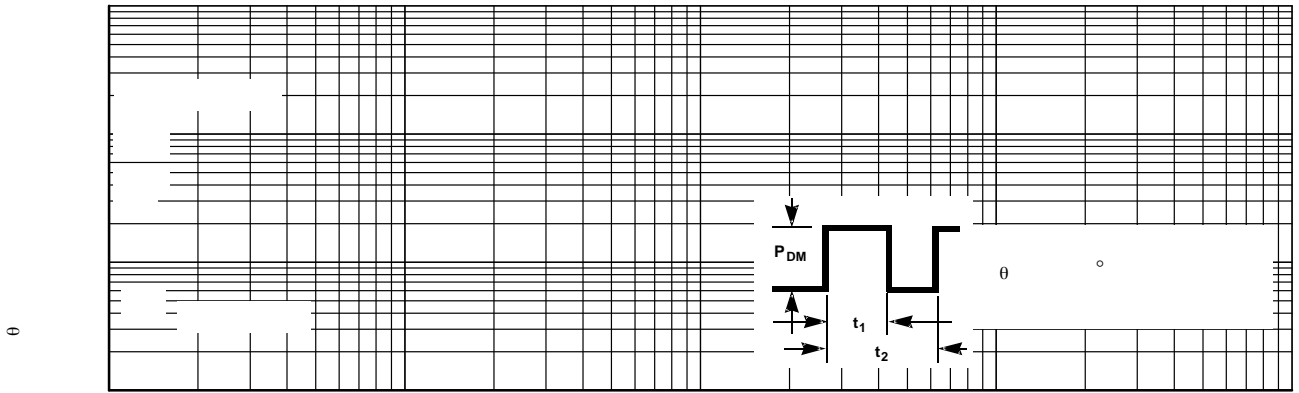
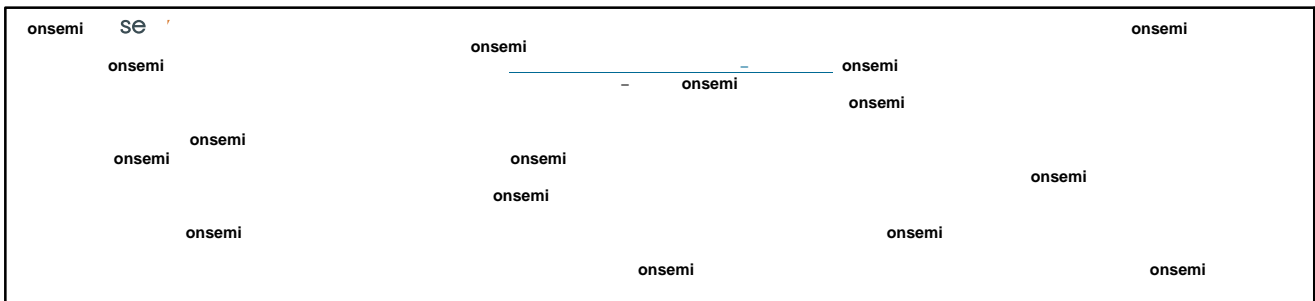


Figure 13. Junction-to-Case Thermal Response

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PACKAGE DIMENSIONS

TO-



ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS

Technical Library: _____
onsemi Website: _____

ONLINE SUPPORT

For additional information, please contact your local Sales Representative at _____